

SSM6J206FE(TE85L,F

SSM6J206FE(TE85L,F Information



For Reference Only

Part Number SSM6J206FE(TE85L,F

Manufacturer Toshiba Semiconductor and Storage

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 20V 2A ES6

Package SOT-563, SOT-666

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SSM6J206FE(TE85L,F Specifications

Manufacturer Toshiba Semiconductor and Storage Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package SOT-563, SOT-666 Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 2A (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4V Vgs(th) (Max) @ Id 1V @ 1mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 335pF @ 10V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 500mW (Ta) Rds On (Max) @ Id, Vgs 130 mOhm @ 1A, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package ES6 (1.6x1.6) Package / Case SOT-563, SOT-666	Manufacture Deat Namber	CCMCIOCEE/TEOSI E
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PackageSOT-563, SOT-666Series-FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C2A (Ta)Drive Voltage (Max Rds On, Min Rds On)1.8V, 4VVgs(th) (Max) @ Id1V @ 1mAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds335pF @ 10VVgs (Max)±8VFET Feature-Power Dissipation (Max)500mW (Ta)Rds On (Max) @ Id, Vgs130 mOhm @ 1A, 4VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageES6 (1.6x1.6)Package / CaseSOT-563, SOT-666	Category	Discrete Semiconductor Products
Series-FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C2A (Ta)Drive Voltage (Max Rds On, Min Rds On)1.8V, 4VVgs(th) (Max) @ Id1V @ 1mAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds335pF @ 10VVgs (Max)±8VFET Feature-Power Dissipation (Max)500mW (Ta)Rds On (Max) @ Id, Vgs130 mOhm @ 1A, 4VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageES6 (1.6x1.6)Package / CaseSOT-563, SOT-666		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 2A (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4V Vgs(th) (Max) @ Id 1V @ 1mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 335pF @ 10V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 500mW (Ta) Rds On (Max) @ Id, Vgs 130 mOhm @ 1A, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package ES6 (1.6x1.6) Package / Case SOT-563, SOT-666	Package	SOT-563, SOT-666
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 2A (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4V Vgs(th) (Max) @ Id 1V @ 1mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 130 mOhm @ 1A, 4V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case MOSFET (Metal Oxide) 20V 20V 20V 20V 21A (Ta) 1.8V, 4V 1.8V 4.8V - - 1.8V 4.8V 500mW (Ta) 1.30 mOhm @ 1A, 4V 4.4V 50 mounting Type Surface Mount Supplier Device Package ES6 (1.6x1.6) Package / Case	Series	-
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 2A (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4V Vgs(th) (Max) @ Id 1V @ 1mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) 48V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 130 mOhm @ 1A, 4V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case SOT-563, SOT-666	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4V Vgs(th) (Max) @ Id 1V @ 1mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 130 mOhm @ 1A, 4V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case 2A (Ta) 2A (Ta) 2A (Ta) 2A (Ta) 2A (Ta) 2B (Ta) 18V, 4V 18V 18V - 18V 19U 19U 19U 19U 19U 19U 19U 19	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 1V @ 1mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 130 mOhm @ 1A, 4V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case 1.8V, 4V 10 ImA 10 ImA 10 ImA 11 Ima 12 Ima 13 Ima 13 Ima 14 Ima 15 Ima 16 Ima 1	Drain to Source Voltage (Vdss)	20V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 130 mOhm @ 1A, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package ES6 (1.6x1.6) Package / Case SOT-563, SOT-666	Current - Continuous Drain (Id) @ 25°C	2A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 130 mOhm @ 1A, 4V Operating Temperature Mounting Type Surface Mount Supplier Device Package ES6 (1.6x1.6) Package / Case SOT-563, SOT-666	Drive Voltage (Max Rds On, Min Rds On)	1.8V, 4V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±8V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 130 mOhm @ 1A, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package ES6 (1.6x1.6) Package / Case SOT-563, SOT-666	Vgs(th) (Max) @ Id	1V @ 1mA
Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 500mW (Ta) Rds On (Max) @ Id, Vgs 130 mOhm @ 1A, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package ES6 (1.6x1.6) Package / Case SOT-563, SOT-666	Gate Charge (Qg) (Max) @ Vgs	-
FET Feature - Power Dissipation (Max) 500mW (Ta) Rds On (Max) @ Id, Vgs 130 mOhm @ 1A, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package ES6 (1.6x1.6) Package / Case SOT-563, SOT-666	Input Capacitance (Ciss) (Max) @ Vds	335pF @ 10V
Power Dissipation (Max) 500mW (Ta) Rds On (Max) @ Id, Vgs 130 mOhm @ 1A, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package ES6 (1.6x1.6) Package / Case SOT-563, SOT-666	Vgs (Max)	±8V
Rds On (Max) @ Id, Vgs130 mOhm @ 1A, 4VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageES6 (1.6x1.6)Package / CaseSOT-563, SOT-666	FET Feature	-
Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package ES6 (1.6x1.6) Package / Case SOT-563, SOT-666	Power Dissipation (Max)	500mW (Ta)
Mounting Type Surface Mount Supplier Device Package ES6 (1.6x1.6) Package / Case SOT-563, SOT-666	Rds On (Max) @ Id, Vgs	130 mOhm @ 1A, 4V
Supplier Device Package ES6 (1.6x1.6) Package / Case SOT-563, SOT-666	Operating Temperature	150°C (TJ)
Package / Case SOT-563, SOT-666	Mounting Type	Surface Mount
· ·	Supplier Device Package	ES6 (1.6x1.6)
Report errors?	Package / Case	SOT-563, SOT-666
Report errors:		Report errors?

SSM6J206FE(TE85L,F Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SSM6J206FE(TE85L,F Payment Methods



















SSM6J206FE(TE85L,F Shipping Methods













If you have any question about SSM6J206FE(TE85L,F, please do not hesitate to contact us!

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